1-Line Uni-directional TVS Diode

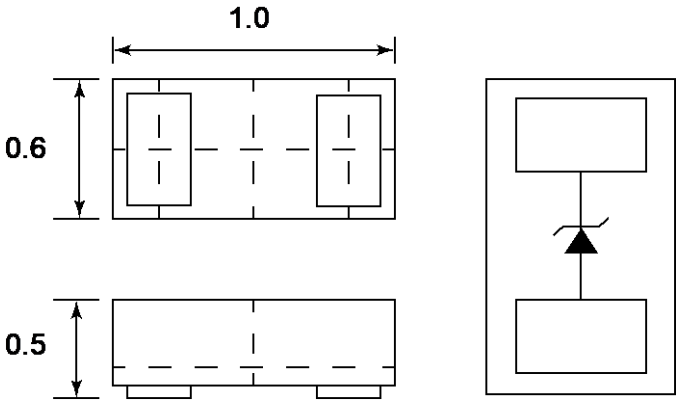
Description

The PESDU2401P1 is a 24V uni-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU2401P1 complies with IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD protection make PESDU2401P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Ultra small package: 1.0x0.6x0.5mm
- Protects one data or power line
- Operating voltage: 24V
- 2-pin leadless package
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±30kV
    - Contact discharge: ±30kV
  - IEC61000-4-5 (Lightning) 5A (8/20μs)
- RoHS Compliant

Dimensions and Pin Configuration



Package Dimensions

Circuit and Pin Schematic

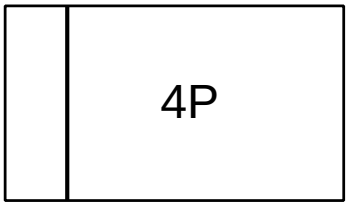
Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players

Marking Information



4P = Device Marking Code
Bar denotes cathode

Ordering Information

Part Number	Shipping	Reel Size
PESDU2401P1	10000/Tape & Reel	7 inch

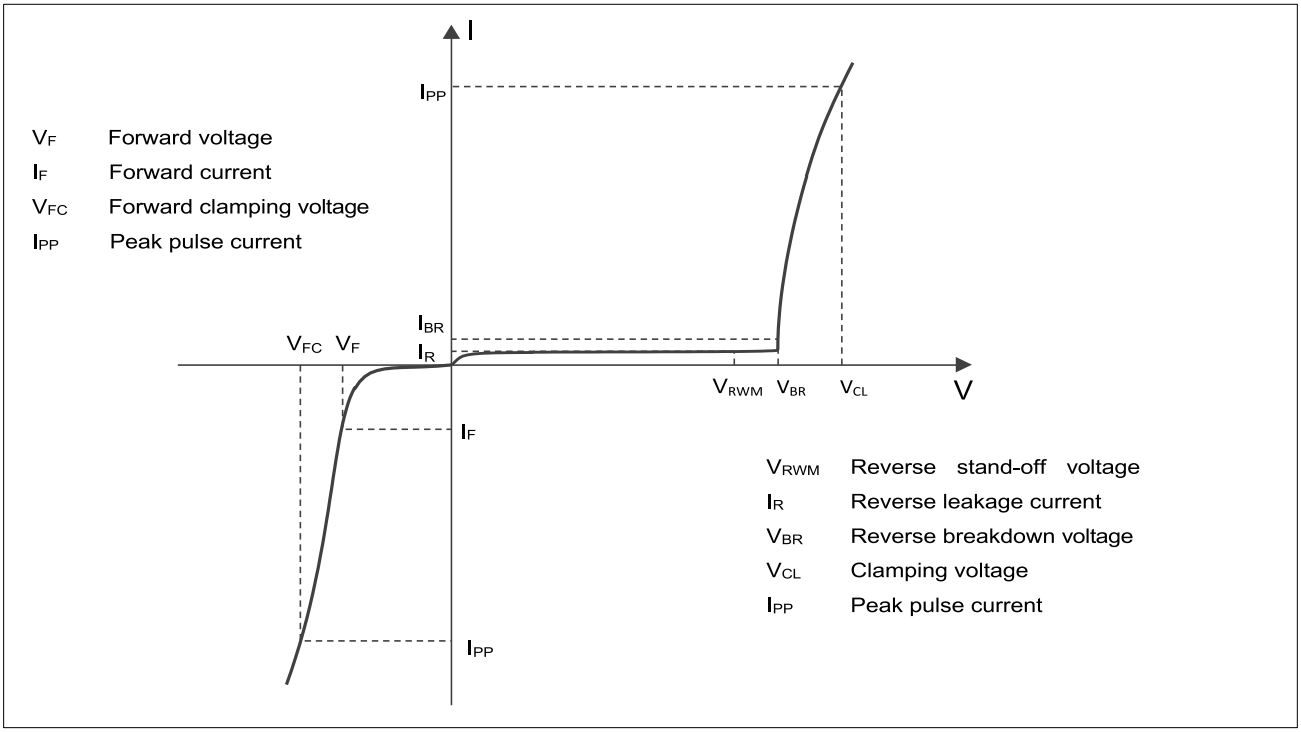
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P_{PK}	220	W
Peak Pulse Current (8/20μs)	I_{PP}	5	A
ESD per IEC 61000−4−2 (Air)	V_{ESD}	±30	kV
ESD per IEC 61000−4−2 (Contact)		±30	
Lead temperature	T_L	260	℃
Operating Temperature Range	T_{OP}	−40 ~ +85	℃
Storage Temperature Range	T_{STG}	−55 ~ +150	℃

Electrical Characteristics (T_A=25°C unless otherwise specified)

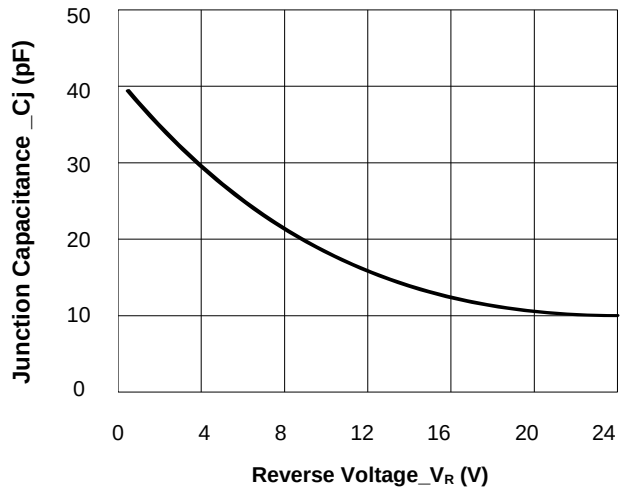
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			24	V	
Breakdown Voltage	V_{BR}	25.9			V	I_T = 1mA
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 24V
Clamping Voltage	V_C			33	V	I_{PP} = 1A (8/20μs pulse),
Clamping Voltage	V_C			44	V	I_{PP} = 5A (8/20μs pulse),
Junction Capacitance	C_J		40		pF	V_R = 0V, f = 1MHz

Electrical characteristics (T_A = 25℃, unless otherwise noted)

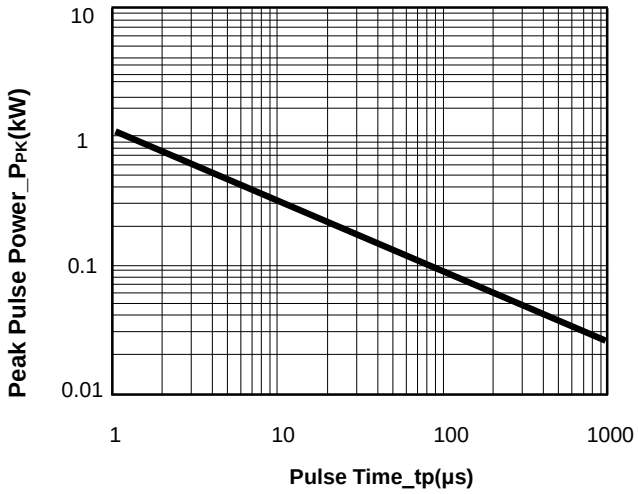


Definitions of electrical characteristics

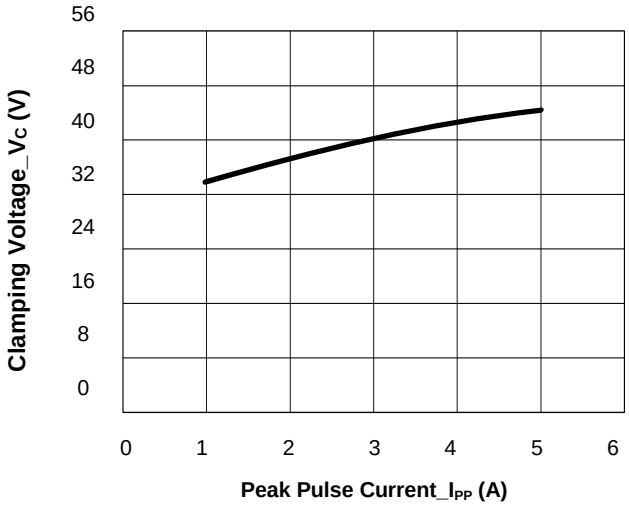
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



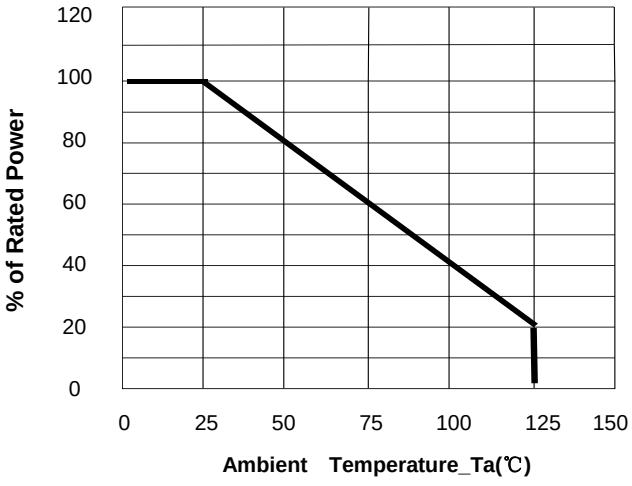
Junction Capacitance vs. Reverse Voltage



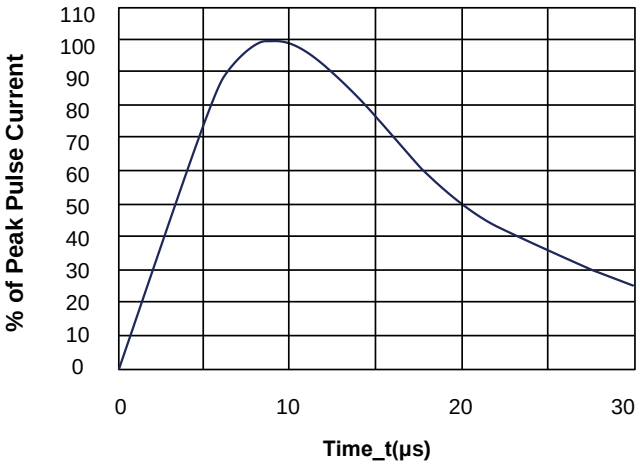
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

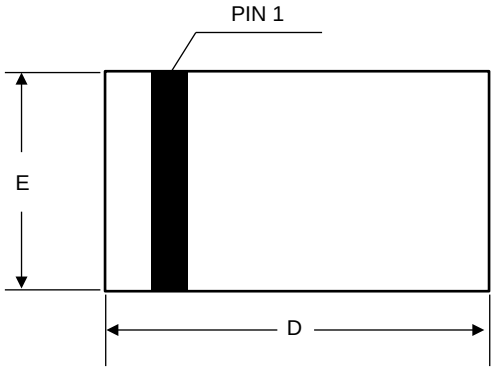


Power Derating Curve

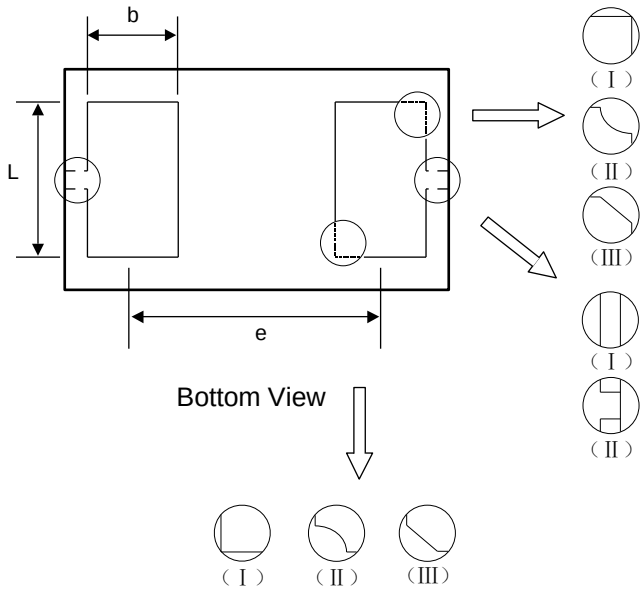


8/20μs Pulse Waveform

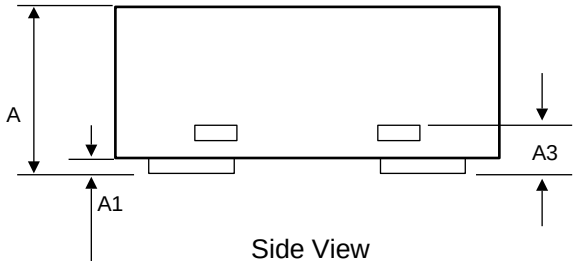
DFN1006-2 Package Outline Drawing



Top View



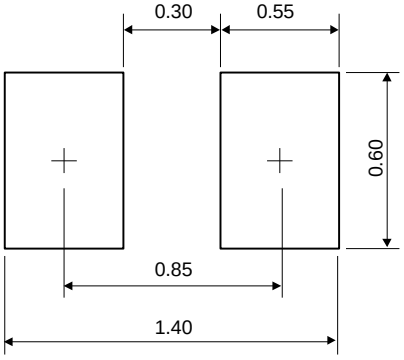
Bottom View



Side View

Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.340	0.450	0.550
A1	0.000	0.020	0.050
A3	0.125 Ref.		
D	0.950	1.000	1.075
E	0.490	0.600	0.675
b	0.200	0.250	0.300
L	0.450	0.500	0.550
e	0.650 BSC		

Recommended PCB Layout (Unit: mm)

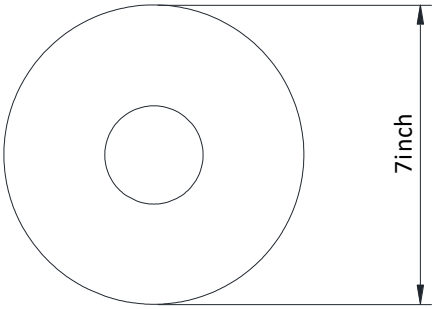


Notes:

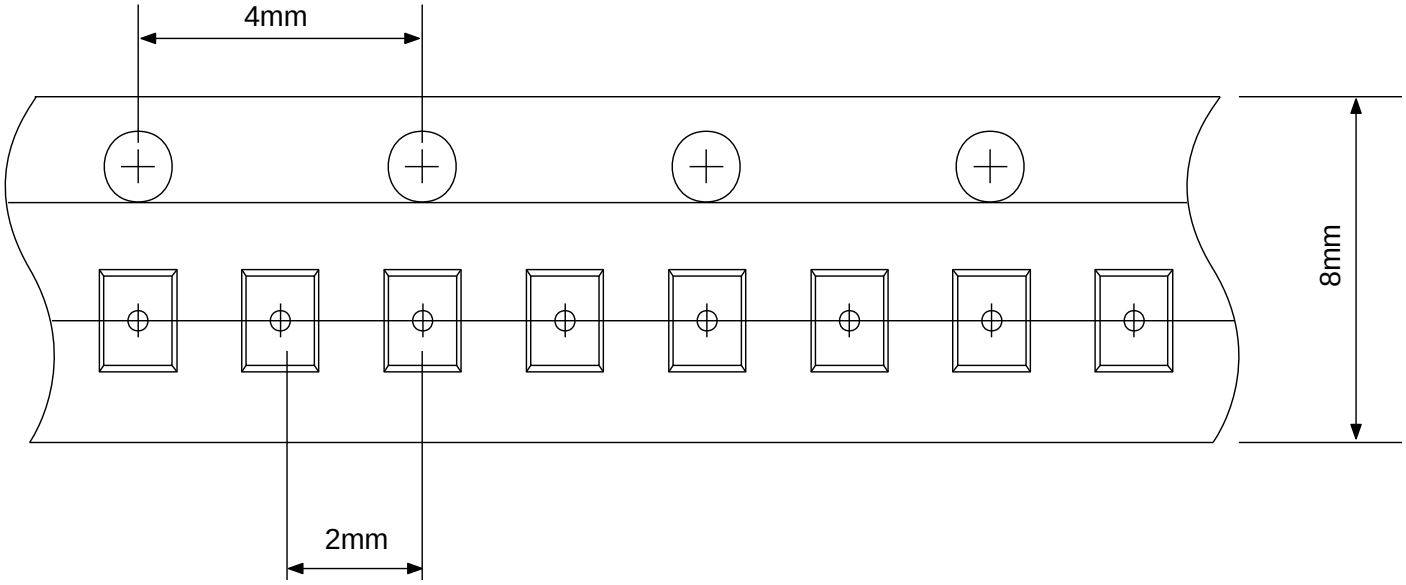
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

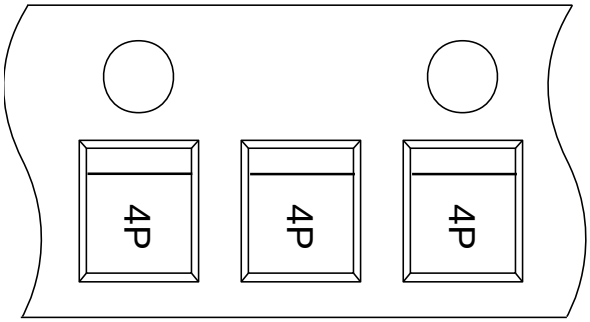
TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions





User Direction of Feed

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